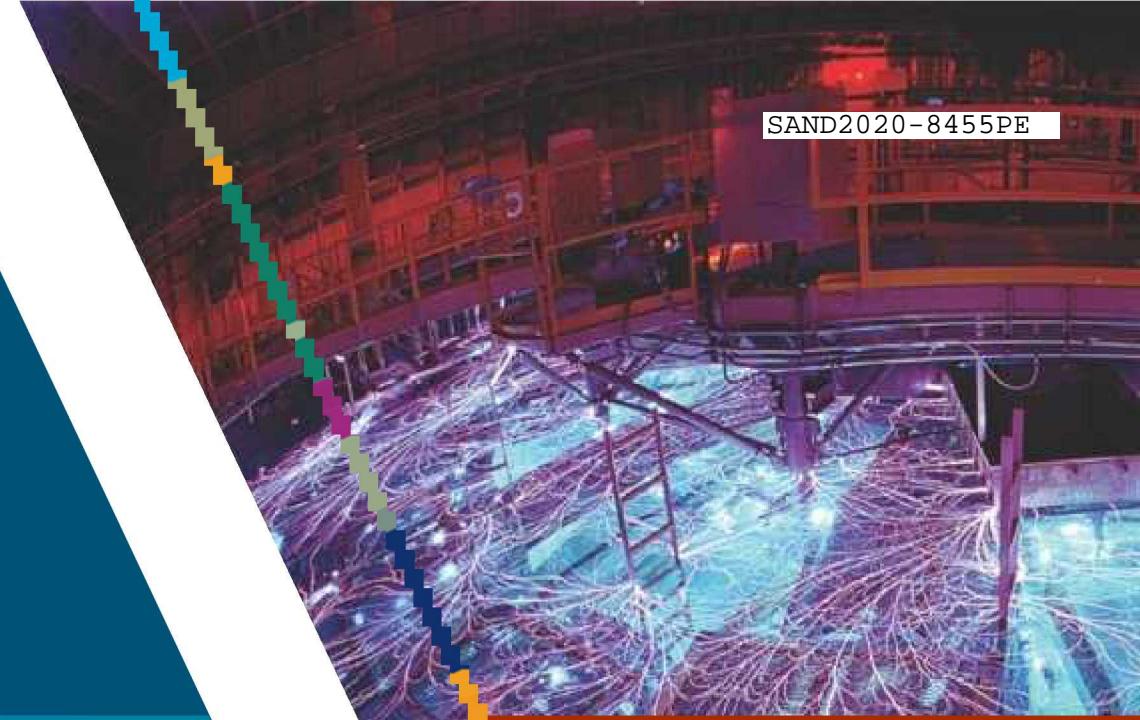




Exceptional service in the national interest

SAND2020-8455PE 1



Sandia's Quantum Photonics Research Foundry

Dr. Michael Gehl, Senior Member of Technical Staff
National Security Photonic Center

Sandia National Laboratories is a multimission laboratory managed and operated by National Technology and Engineering Solutions of Sandia LLC, a wholly owned subsidiary of Honeywell International Inc. for the U.S. Department of Energy's National Nuclear Security Administration under contract DE-NA0003525. SAND

Quantum Facilities & Capabilities

Built on significant investments over 15 years

- Over **70 projects** (**>\$135M**) funded by **Laboratory Directed Research and Development (LDRD)**
- Many projects funded by DOE & OGA (IARPA, DARPA, NIH, LPS,...). Over \$100M to date.
- >150 staff involved in quantum at Sandia

Unique, hard-to-replicate capabilities

- Producing quantum devices in **multiple qubit technologies**
- Deep understanding of how device **architecture** impacts quantum applications and algorithms
- Facilities: **MESA fab**, **Center for Integrated Nanotechnologies (CINT)**, **Ion Beam Lab (implantation)**, **High Performance Computing**

Trusted advisor to multiple government agencies

- Key agency rotations and workshop leadership



MESA



CINT



IBL

Quantum Facilities & Capabilities

Microsystems Engineering, Science and Applications

- Co-located research & production
- Currently dozens of products: ASICs, III-V SSICs, MEMS, FPAs, RFICs, Optoelectronics
- 400,000 Square Foot Complex, >650 Employees
- Co-located CMOS Foundry and Compound Semiconductor Fabrication



MESA



CINT



IBL

Quantum Facilities & Capabilities

Center for Integrated Nano-Technology (CINT)

Quantum – Dr. Michael Lilly, mplilly@sandia.gov

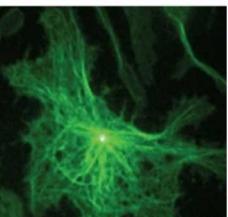
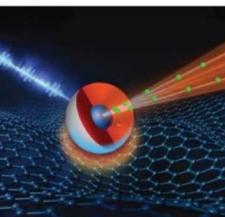
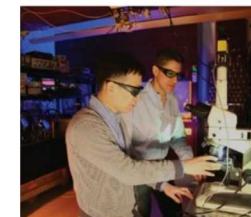
Photonics – Dr. Igal Brener, ibrener@sandia.gov

Research areas:

- **In-Situ Characterization & Nanomechanics** – Developing and implementing world-leading capabilities to study the dynamic response of materials and nanosystems to mechanical, electrical, or other stimuli.
- **Nanophotonics & Optical Nanomaterials** – Synthesis, excitation, and energy transformations of optically active nanomaterials and collective or emergent electromagnetic phenomena (plasmonics, metamaterials, photonic lattices).
- **Soft, Biological & Composite Nanomaterials** – Synthesis, assembly, and characterization of soft, biomolecular, and composite nanomaterials that display emergent functionality.
- **Quantum Materials Systems** – Understanding and controlling quantum effects of nanoscale materials and their integration into systems spanning multiple length scales.



<https://cint.lanl.gov>
<https://cint.sandia.gov>
cint@lanl.gov



MESA



CINT



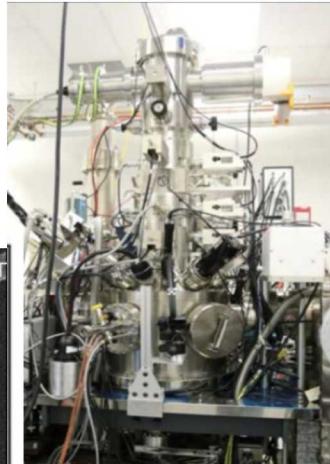
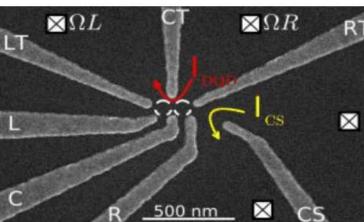
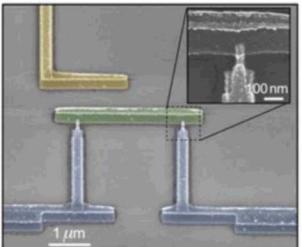
IBL

Quantum Facilities & Capabilities

Center for Integrated Nano-Technology (CINT)

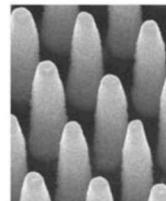
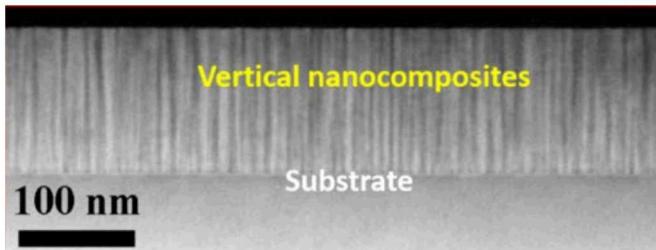
Quantum Information Science

- Quantum Transport and qubits
- Quantum Sensing
- Focused ion implantation



Materials synthesis

- Ultra-High Mobility MBE
- Complex Oxide PLD
- CVD Nanowire Growth



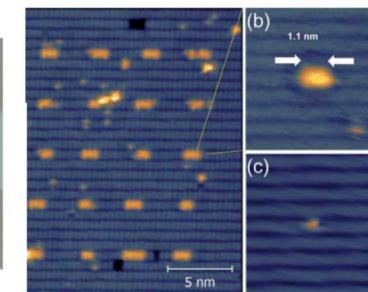
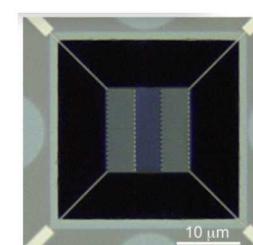
Theory for Correlated Systems

- Techniques for strongly correlated models
- Many-body approaches
- Mean-field modeling for quantum materials



Forefront Lithography

- Atomic-Precision Lithography
- Nanoscale devices

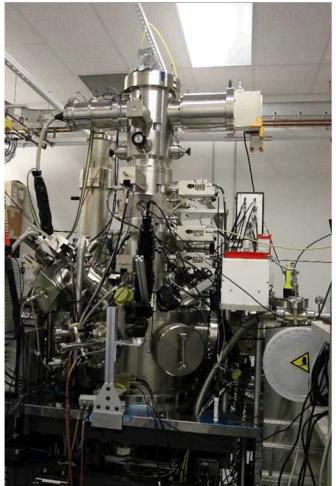
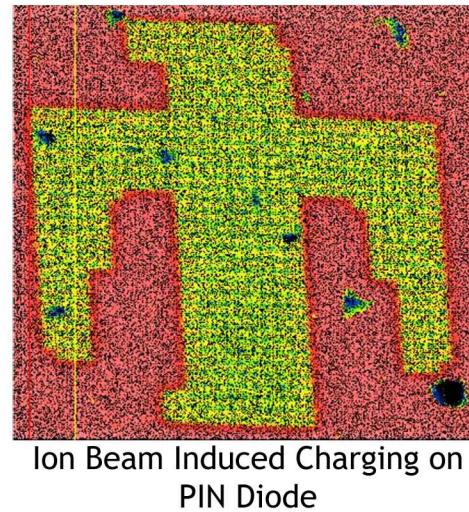


Quantum Facilities & Capabilities

Ion Beam Laboratory (IBL)

Dr. Edward Bielejec, esbiele@sandia.gov

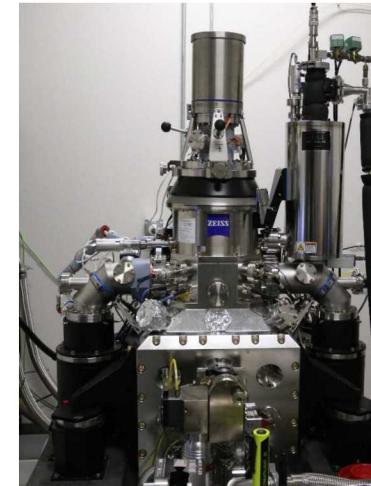
- 6 Operational micro/nano implant systems
 - Spot sizes from 0.5nm to mm's
 - Energies from 5keV to 70MeV
 - Single ion implantation
 - <40nm targeting resolution possible
- 26 ion species in use, 40+ ions possible



100 keV A&D FIB100NI



35 keV Raith Velion



100 keV Zeiss Orion Plus



MESA

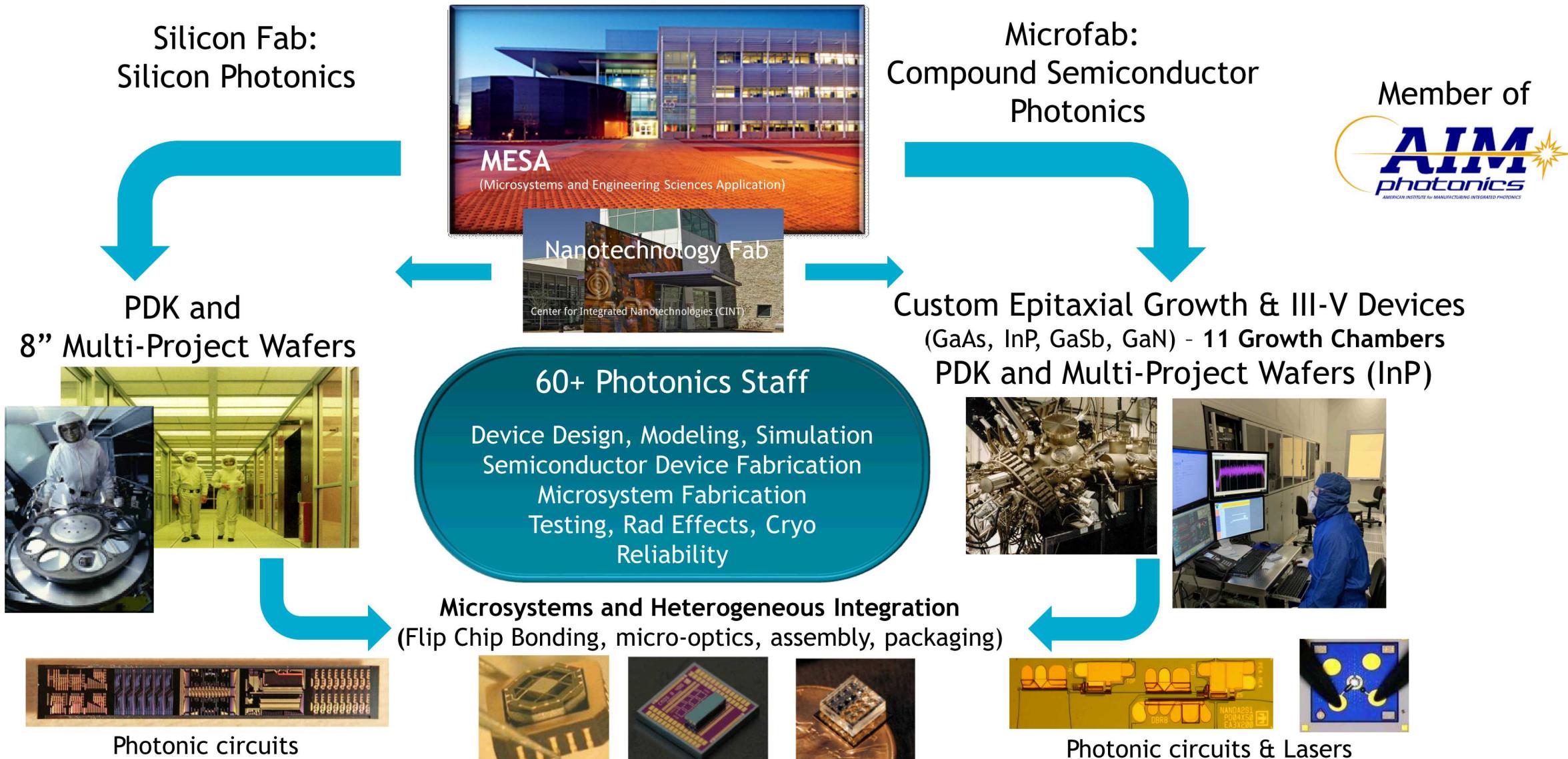


CINT



IBL

Sandia's National Security Photonic Center



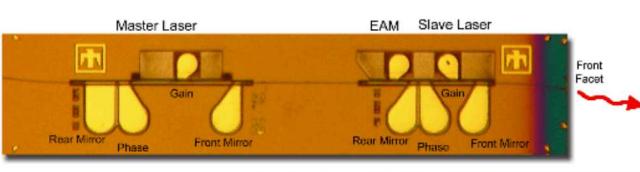
8 Multi-Project Wafer Offerings

InP Photonics

- 3 tier offerings at 1550nm**
 - Tier 1: one regrowth
 - Tier 2: 2 regrowths (High P_{sat} Amplifier)
 - Tier 3: Full custom process



RF-Optical Channelizing Filter
1-20 GHz RF on C-Band Light



Master Laser EAM Slave Laser
Gain Gain
Rear Mirror Rear Mirror Phase Front Mirror Front Mirror
On-Chip Injection Locking
Enhanced Modulation > 50 GHz, C-Band

For more information:
photonics@sandia.gov

Silicon Photonics

- MPW Device Library**
 - 20 Active, 22 Passive Components
 - Synopsis OptoDesigner
 - 200mm SOI Platform
 - Three Deliverables
 - Passive
 - Passive + Active
 - Passive + Active + Germanium

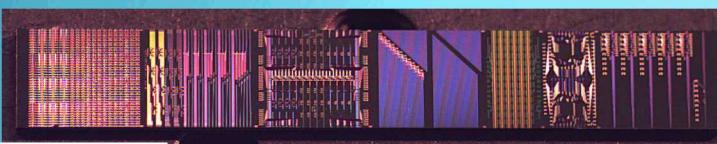
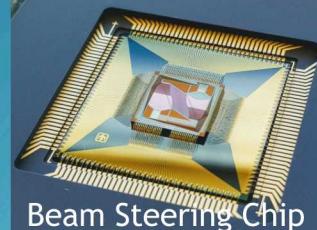


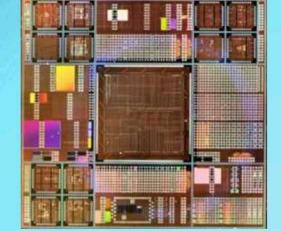
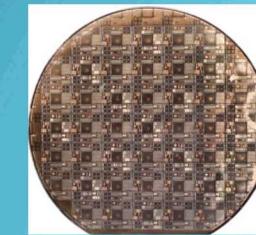
Image of MPW run, supporting Columbia, U of AZ, UC Berkeley, UCSD & Caltech

CLAN CENTER FOR ADVANCED NETWORKS

Ring Filter with Heater
Filter w/ wavelength stabilization
Through Port
Drop Port Tap
Thermal Phase Shifter
MZI-DC
Ge Detectors

CMOS7

- Multiple Engagement Models**
 - Full design & implementation by customer
 - Full design & implementation by Sandia
 - Anywhere in between
- Non-Standard, custom processes**
 - AlN for resonators
 - Large-area graphene deposition
 - Deep trench capacitors
 - Prototype non-volatile memory
 - Thick metal
 - RF devices

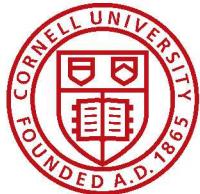
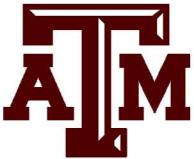
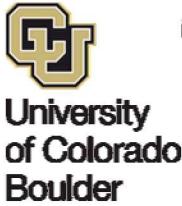


MPW & CMOS Design Contact:

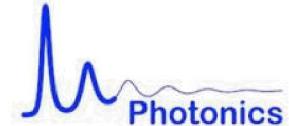
Ann Petersen, Manager
Advanced CMOS Products/Design
505-844-3160
annpete@sandia.gov

Photonics Collaborators & Sponsors

University



Small Business



Large Business



A Xerox Company

Government



Office of Science

MESA Capabilities – Silicon Photonics Platform

Dr. Anthony Lentine, allenti@sandia.gov

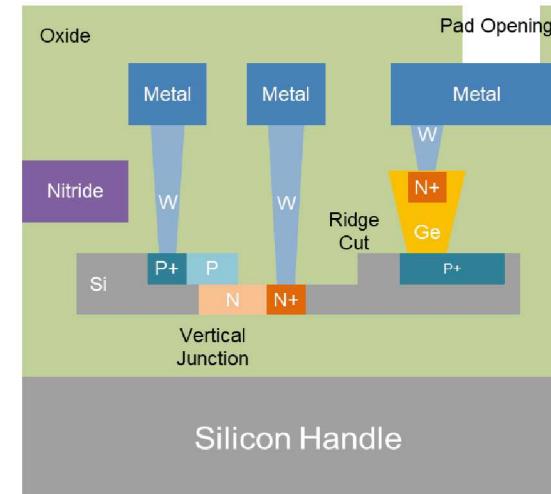
Dr. Michael Gehl, mgehl@sandia.gov

Mature silicon photonics capability developed through 12 years of investment

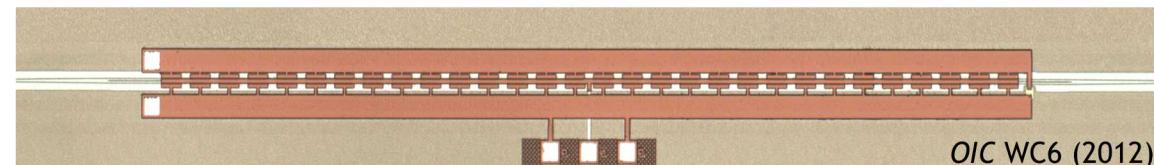
- Low power, high bandwidth modulation & detection
- Low loss optical waveguides (<0.1 dB/cm @ 1550nm)
- 200mm SOI CMOS process
- Silicon, Silicon Nitride & Alumina Waveguides
- Selective area germanium epitaxy
- Cryogenic (<1K) optimized devices

Applications in Quantum

- Quantum Networking/Communication
- Linear Optical Quantum Computing
- Laser Source Generation & Control
- Classical Control & Data Communication



20+ GHz Electro-Optic Modulator



OIC WC6 (2012)

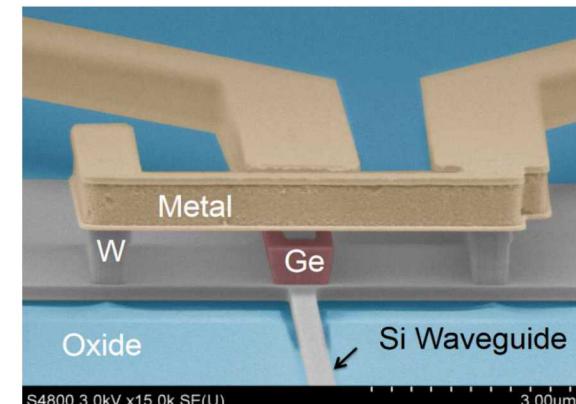
10 Gb/s Cryogenic Optical Modulator



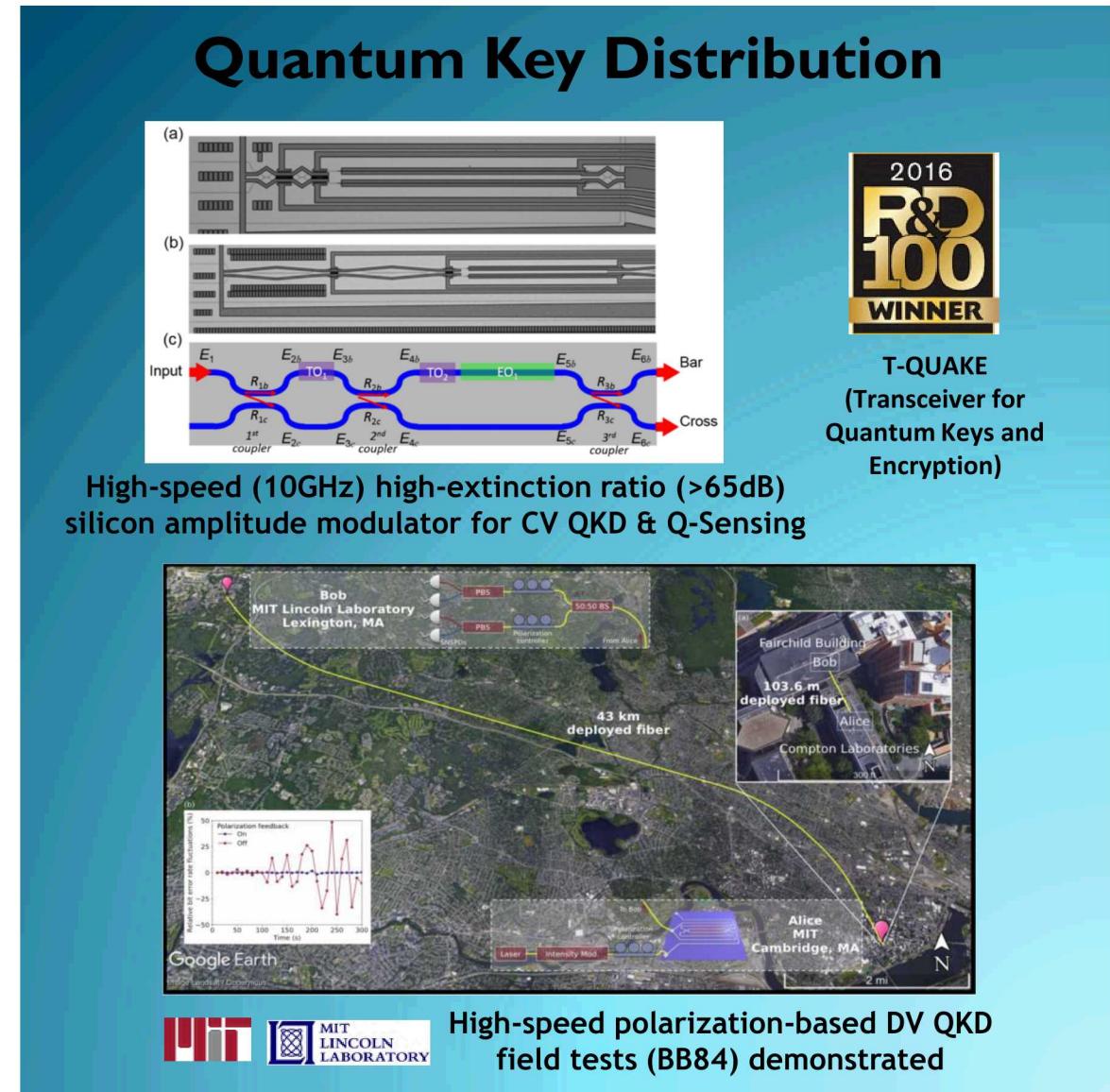
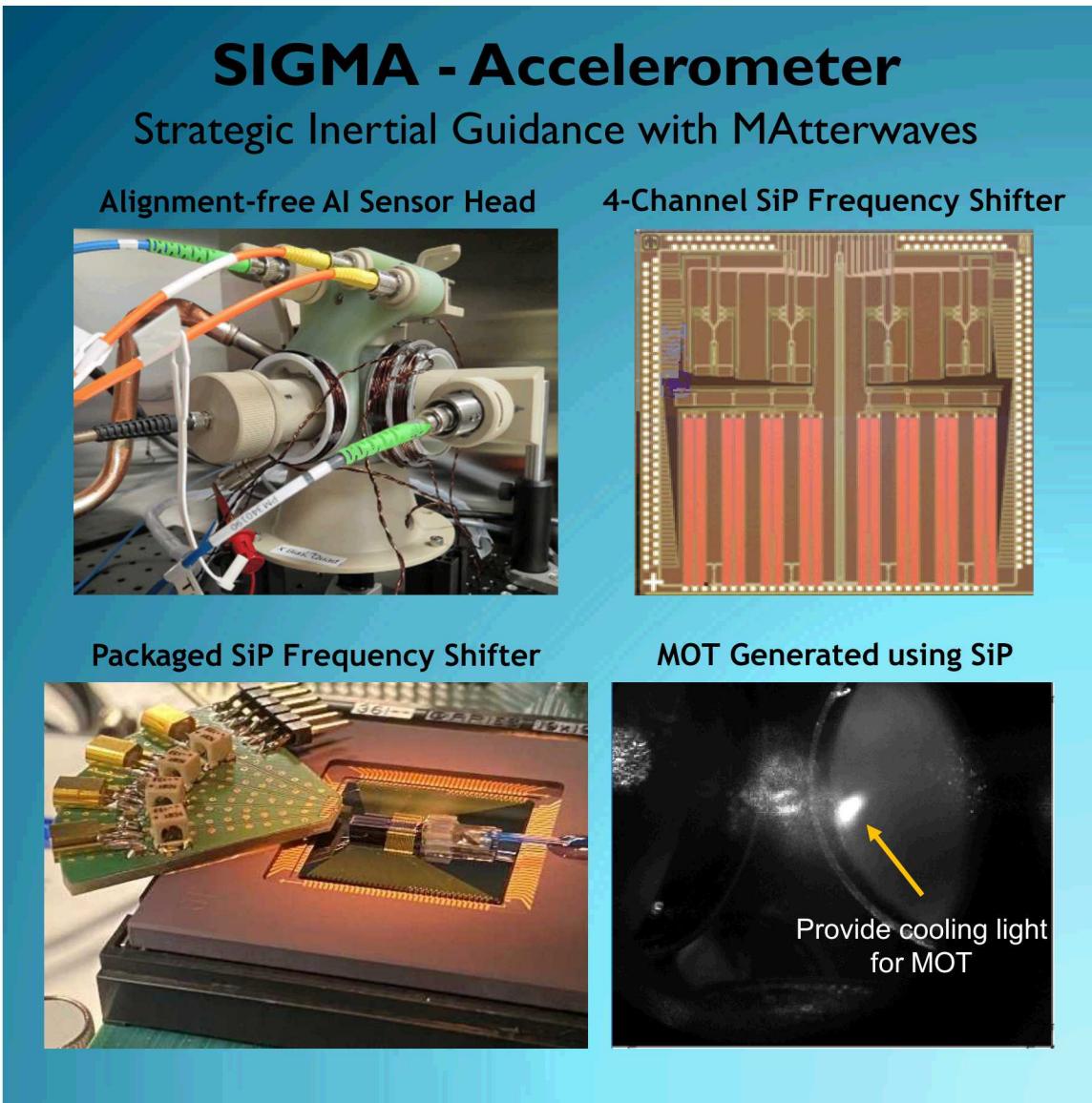
Optica 4, 374 (2017)

Cross section of Sandia's standard silicon photonics process

Ge Single Photon Detector



Optics express 25, 16130 (2017)



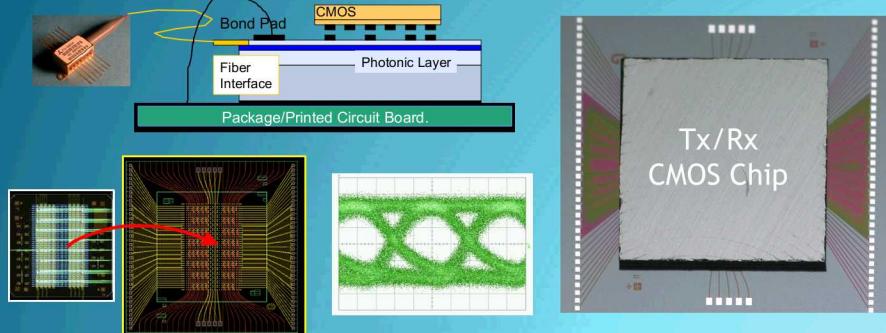
MESA Capabilities – Heterogeneous Integration

Dr. Anthony Lentine, allenti@sandia.gov

Heterogeneous integration enables miniaturization with independent material and device optimization

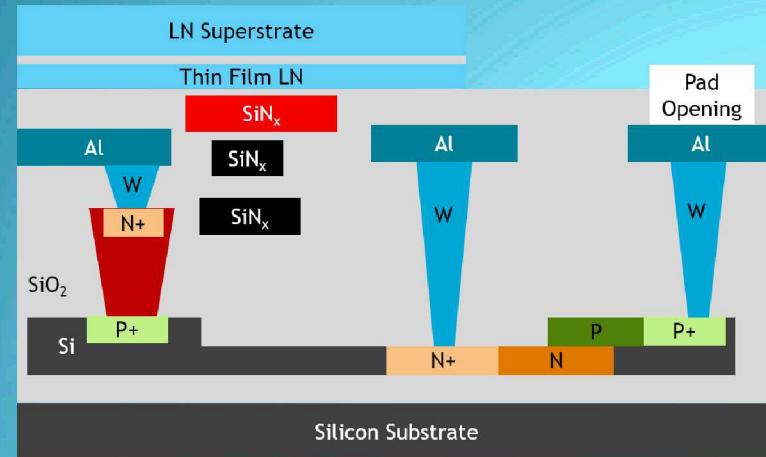
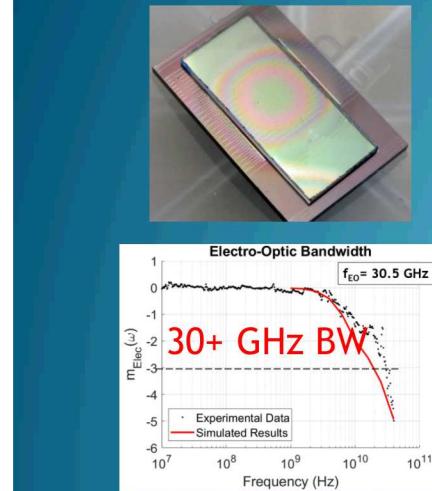
- Integration of LiNbO_3 and III-V Lasers on Silicon Photonics
- Integration of CMOS with InGaAsP/InP , InGa/GaAs , Silicon Photonics, and other materials

CMOS & III-V or Si PICs

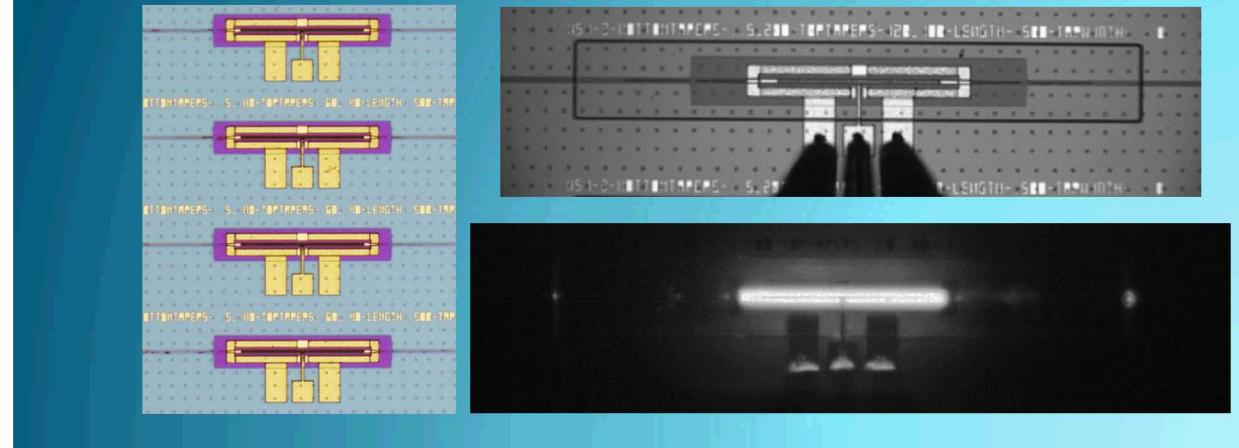


- silicon photonics on high-speed silicon ASIC
- independent optimization of electronics & photonics

Thin Film Lithium Niobate on Si



III-V Lasers & Amplifiers on Si

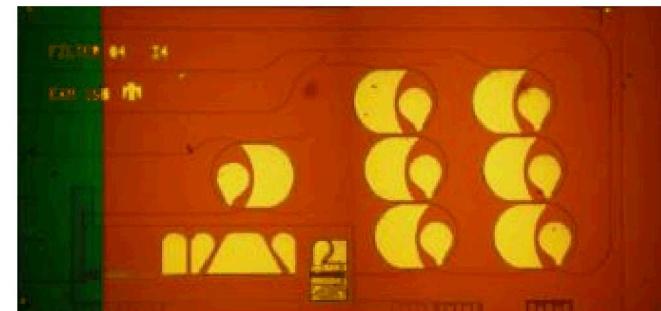


MESA Capabilities – III/V Photonics Platform

Dr. Erik Skogen, ejskoge@sandia.gov

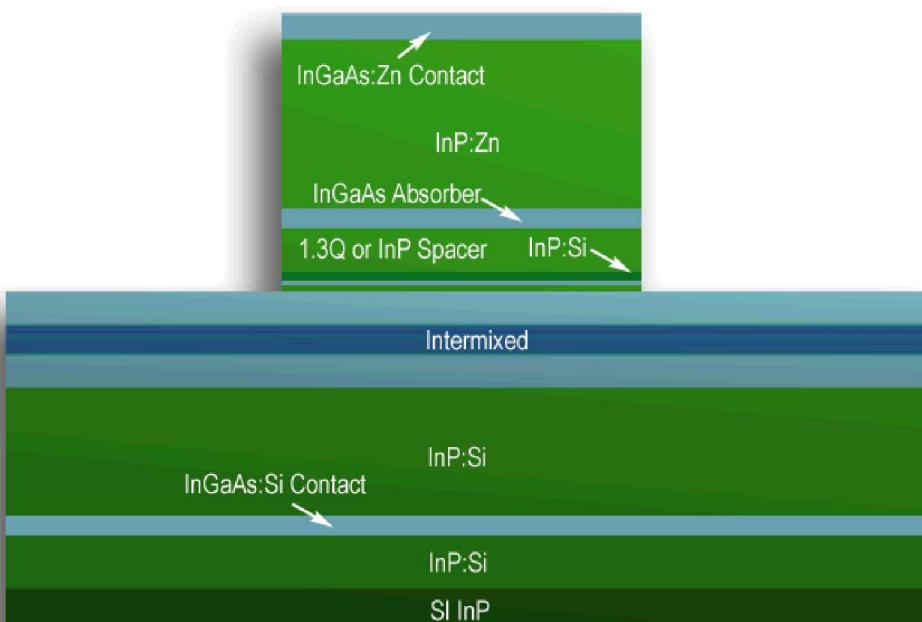
InP-based Photonic Integrated Circuits

- Multiple band-edges by quantum-well-intermixing and/or regrowth
- Single and/or multiple epitaxial regrowth(s)
- Top-side n-type and p-type contacts
- Ridge, buried, and/or deep etch waveguide architectures

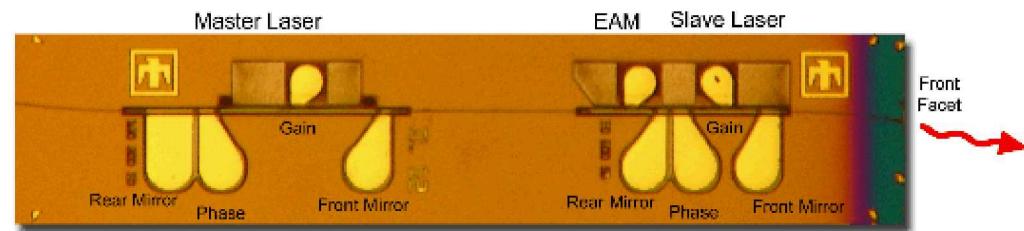


RF-Optical Channelizing Filter 1-20 GHz RF on C-Band Light

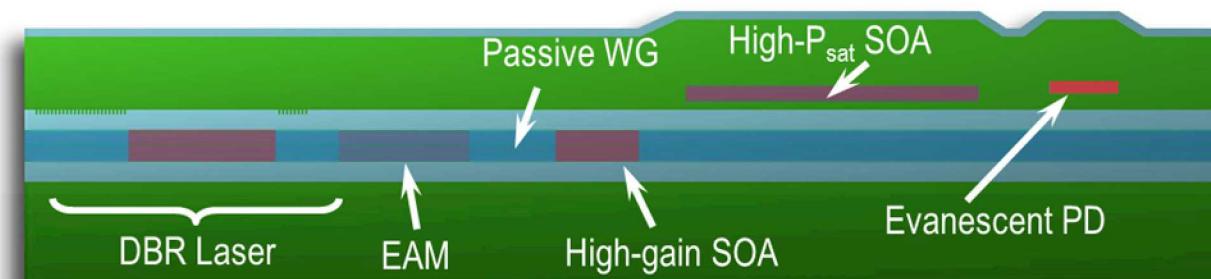
778nm lasers and modulators have been demonstrated



Device Cross-section (Lateral)



On-Chip Injection Locking
Enhanced Modulation > 50 GHz, C-Band



Device Cross-section (Longitudinal)

MESA Capabilities – Nano-Opto-Mechanics (NOMS) & Piezo-Electrics

Dr. Matt Eichenfield, meichen@sandia.gov

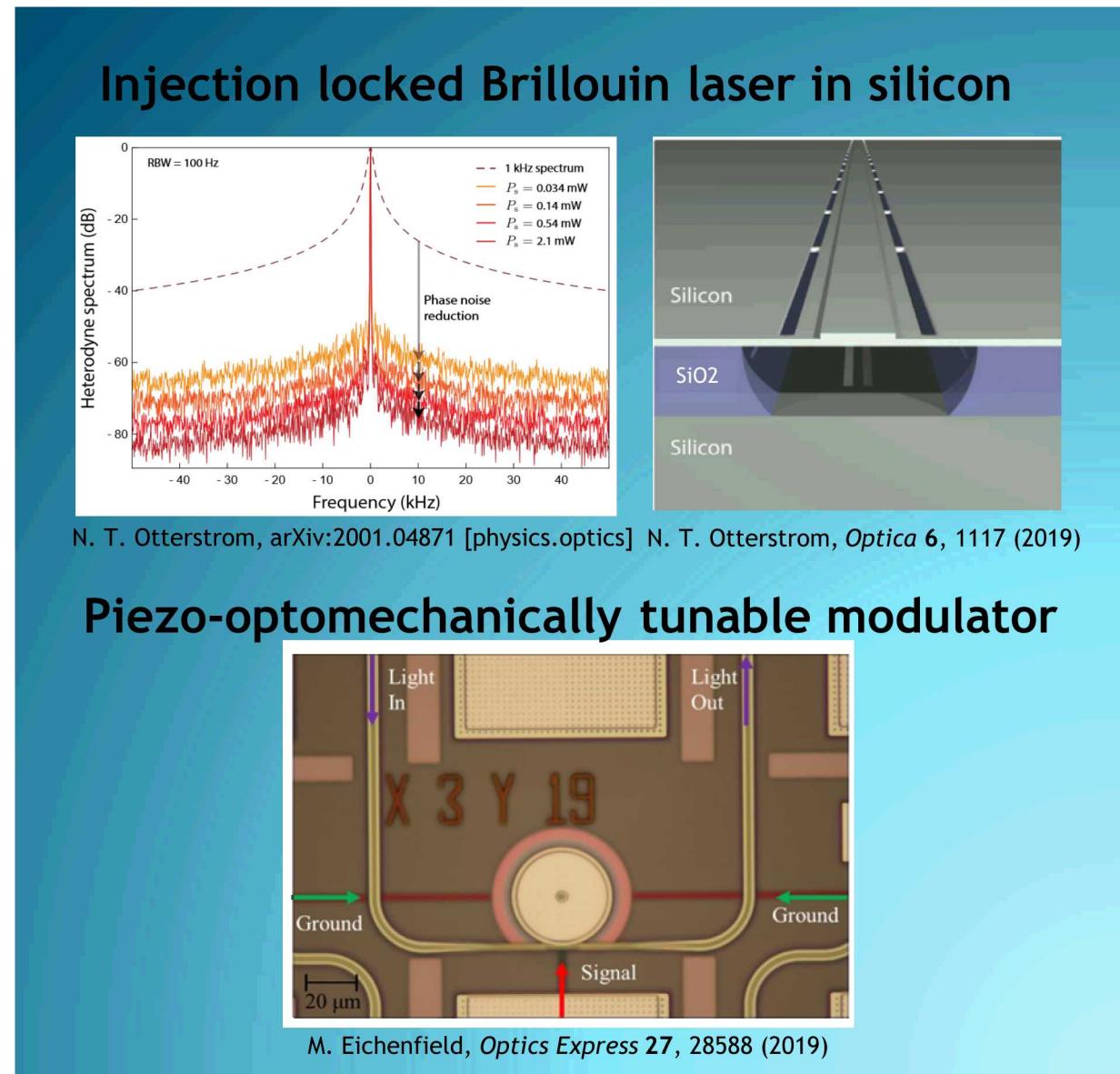
Dr. Nils Otterstrom, ntotter@sandia.gov

Leveraging MEMS expertise to generate new classes of optical devices

- Narrow linewidth filters
- Brillouin amplification & lasing
- Optical isolators
- On-chip delay
- Frequency Shifting
- Modulation & phase shifting

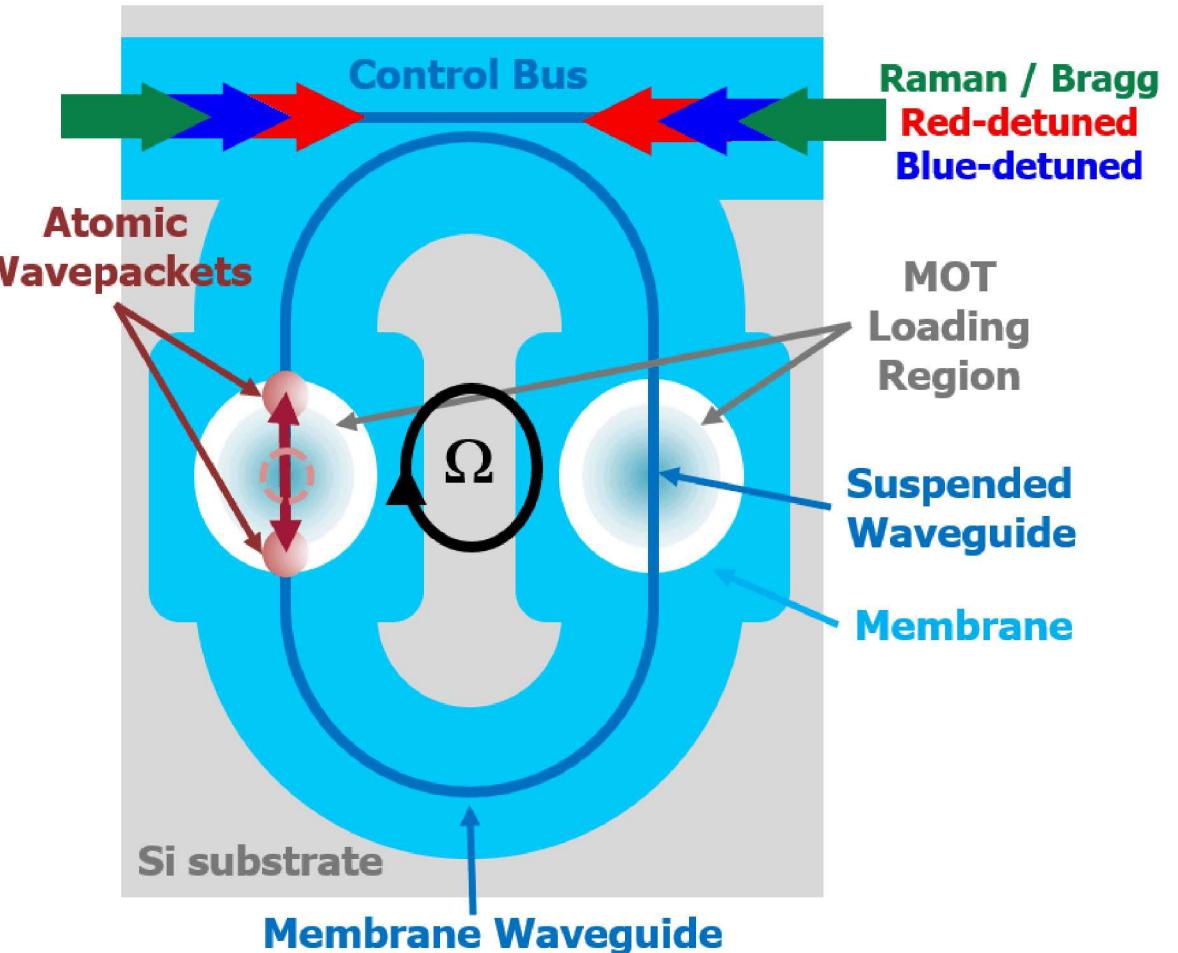
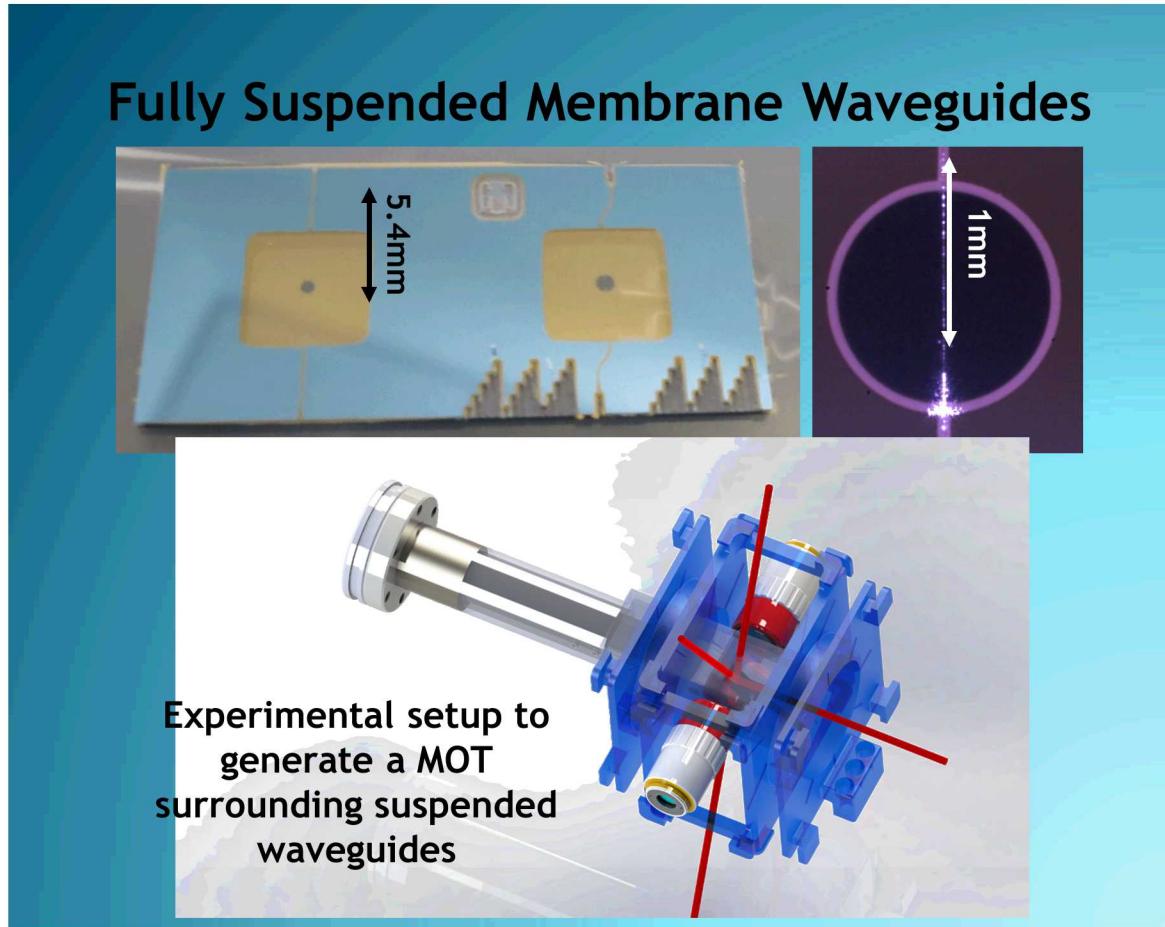
On-going quantum research

- Squeezed states
- Qubit transduction
- Opto-mechanical cooling



Matterwave Sagnac Interferometer

Dr. Jongmin Lee (PI) jlee7@sandia.gov, Dr. Michael Gehl



Atomic-Photonic Integration (A-Phi)

MESA Capabilities – Ion Trapping Platform

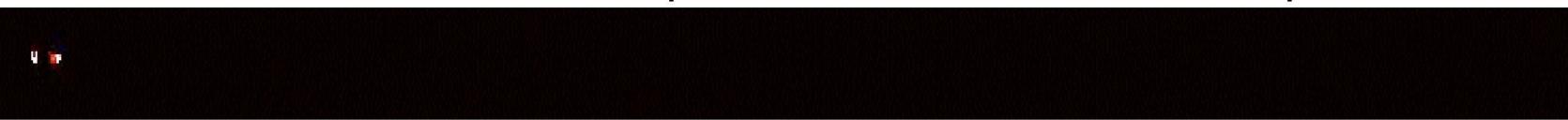
Dr. Daniel Stick, dlstick@sandia.gov

- Fabricating traps for quantum computing since 2005
 - Delivered fully functioning, packaged ion traps to >12 collaborations
 - Integration capabilities include:
high optical access, up to 6 metal levels, low loss UV/Vis optical waveguides,
high performance SPADs, through-trap loading holes/slots, ion shuttling junctions.
- Sandia has demonstrated:
 - Calcium and Ytterbium ion trapping with high fidelity 1- and 2-qubit gate operations
 - Room temperature and cryogenic operation
 - Custom RF and electronic control system for qubit manipulation
 - Custom optical systems for individual addressing and detection of ions in linear chains
 - Low-induced-heating ion shuttling

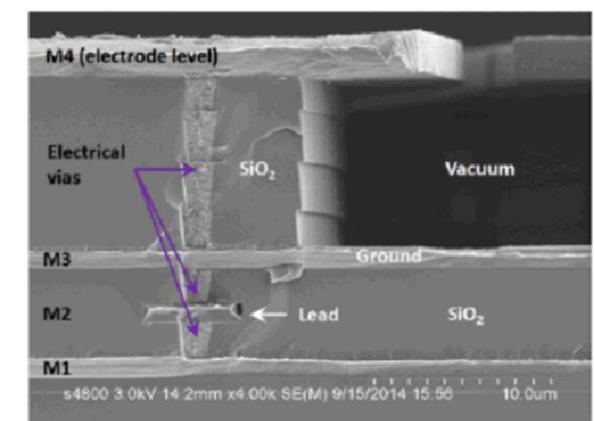
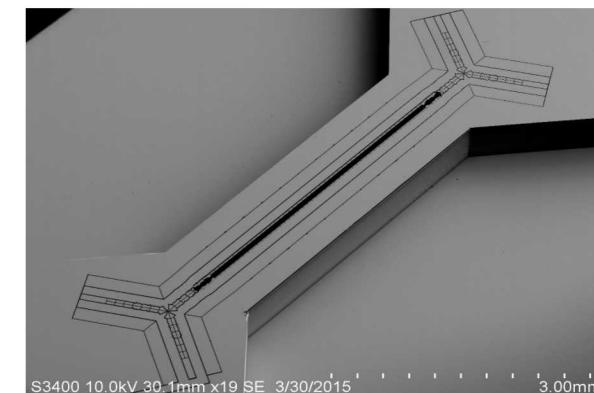
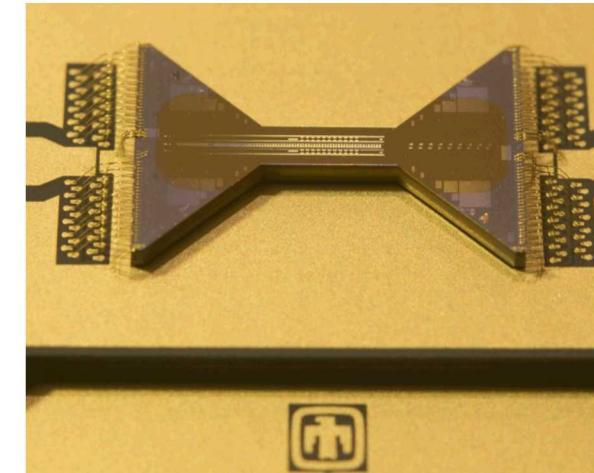
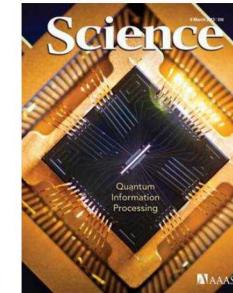
Ion Split/Merge Control Solutions



Demonstration of Sophisticated Ion Control in a Linear Trap



Simultaneous Trapping of 44 Ions in a Single Well



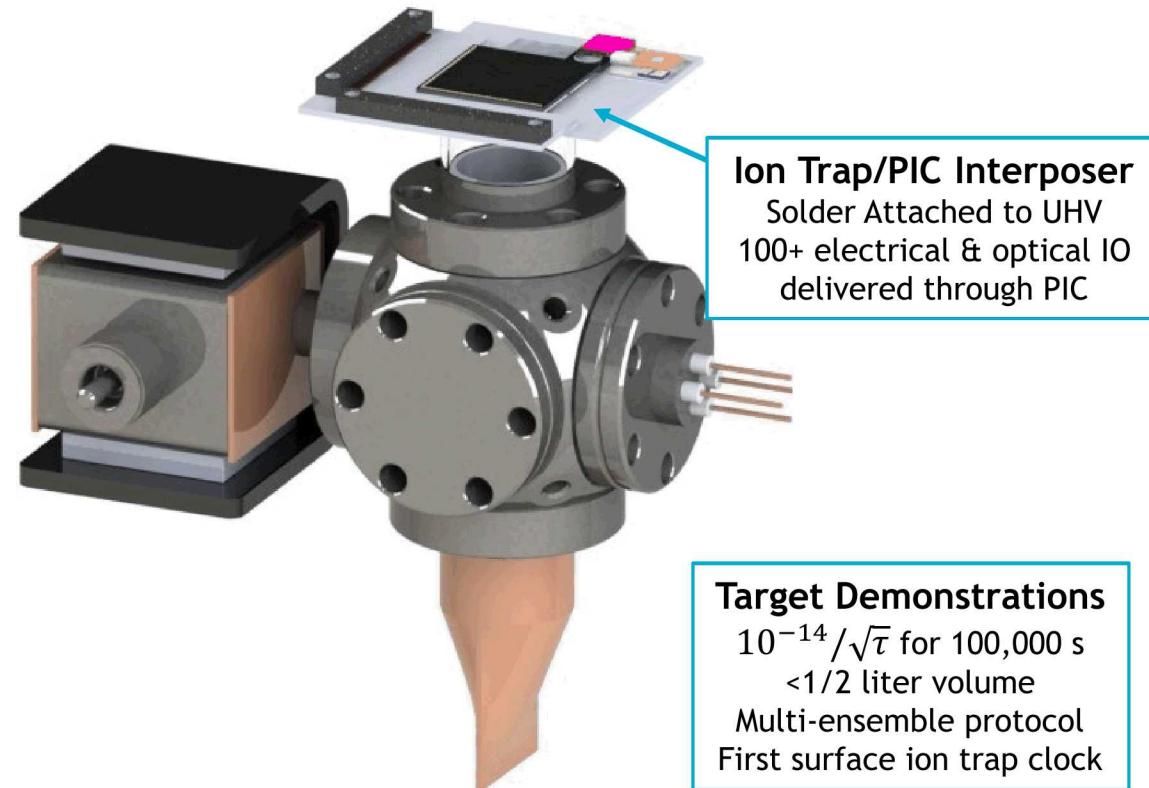
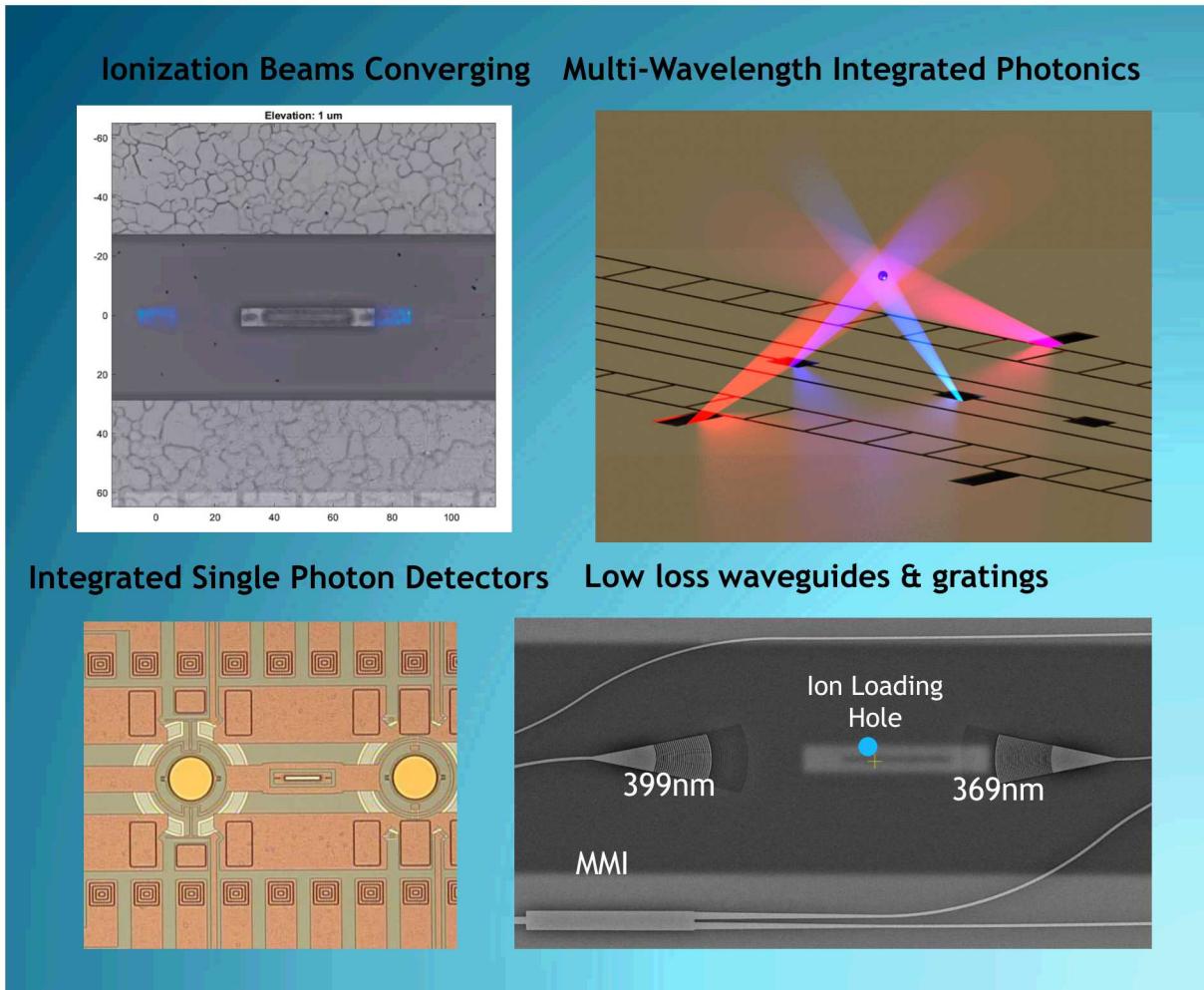
MESA Capabilities – Ion Trapping Platform



TICTOC

Trapped Ion Clock using photonic Technology On Chip

Dr. L. Paul Parazzoli (PI) ipparaz@sandia.gov, Dr. Hayden McGuinness, Dr. Michael Gehl



MESA Capabilities – QSCOUT

Quantum Scientific Computing Open User Testbed

Dr. Susan Clark, sclark@sandia.gov, qscout@sandia.gov

Goals

- Quantum processor for Scientific applications
- High fidelity operations
- Full connectivity between qubits
- Open system, fully specified operations and hardware
- Quantum assembly language enabling low-level access for control down to gate pulses
- Open for vertical integration by users

Realization

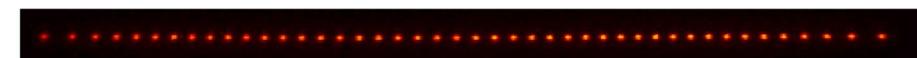
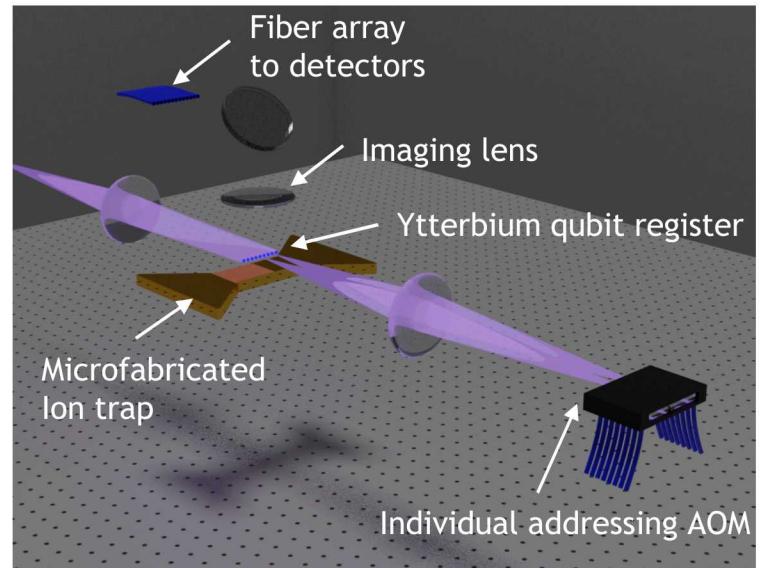
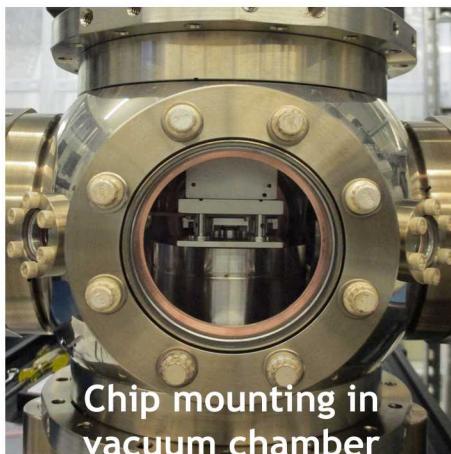
- Trapped ion system using chain of ytterbium-171 ions:
 - Near-ideal prep and measure, no idle errors, lowest gate errors
- Reconfigurable in software
- All-to-all Connectivity

User Access

- In collaboration with SNL QSCOUT scientists
- First round of users includes operations with 3 qubits
- Expected start November 2020
- Calls for user proposals: <https://qscout.sandia.gov>

Current Status

- System design complete
- Realized high-fidelity single-qubit operations
- Qubit Coherence times > 13s



Chain of trapped ions

Gate	Entanglement Infidelity	1/2 Trace Distance	1/2 Diamond-Dist	Eigenvalue Ent. Infidelity	Eigenvalue 1/2 Diamond-Dist
Gi	0.00019	0.000817	--	0.00019	0.001081
Gx	0.00004	0.001003	--	0.000039	0.000073
Gy	0.000001	0.001151	--	3×10 ⁻⁷	0.000876

Measured QSCOUT gate infidelities

Conclusion

15+ years of significant investments resulting in world-class quantum expertise and quantum enabling technologies

- Ion traps
- Neutral atoms
- Donors in silicon
- Diamond vacancies
- Silicon & III/V photonics spanning UV to SWIR

Large number of existing collaborative quantum research projects

- QSCOUT – User testbed
- TICTOC – Compact ion trap clock
- Photonic/CMOS multi-project wafers

Developing a quantum workforce through graduate students, post-docs and early career staff

- 60+ photonic staff, 150+ quantum staff

